

# NTMS4N01R2

## Power MOSFET

### 4.2 Amps, 20 Volts

#### N-Channel Enhancement-Mode Single SO-8 Package

##### Features

- High Density Power MOSFET with Ultra Low  $R_{DS(on)}$  Providing Higher Efficiency
- Miniature SO-8 Surface Mount Package Saving Board Space; Mounting Information for the SO-8 Package is Provided
- $I_{DSS}$  Specified at Elevated Temperature
- Drain-to-Source Avalanche Energy Specified
- Diode Exhibits High Speed, Soft Recovery
- Pb-Free Package is Available

##### Applications

- Power Management in Portable and Battery-Powered Products, i.e.: Computers, Printers, PCMCIA Cards, Cellular & Cordless Telephones

##### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	20	V
Drain-to-Gate Voltage ( $R_{GS} = 1.0 \text{ m}\Omega$ )	$V_{DGR}$	20	V
Gate-to-Source Voltage – Continuous	$V_{GS}$	$\pm 10$	V
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	50	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	2.5	W
Continuous Drain Current @ $25^\circ\text{C}$	$I_D$	5.9	A
Continuous Drain Current @ $70^\circ\text{C}$	$I_D$	4.7	A
Pulsed Drain Current (Note 4)	$I_{DM}$	25	A
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	100	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	1.25	W
Continuous Drain Current @ $25^\circ\text{C}$	$I_D$	4.2	A
Continuous Drain Current @ $70^\circ\text{C}$	$I_D$	3.3	A
Pulsed Drain Current (Note 4)	$I_{DM}$	20	A
Thermal Resistance, Junction-to-Ambient (Note 3)	$R_{\theta JA}$	162	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	0.77	W
Continuous Drain Current @ $25^\circ\text{C}$	$I_D$	3.3	A
Continuous Drain Current @ $70^\circ\text{C}$	$I_D$	2.6	A
Pulsed Drain Current (Note 4)	$I_{DM}$	15	A
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
Single Pulse Drain-to-Source Avalanche Energy – Starting $T_J = 25^\circ\text{C}$ ( $V_{DD} = 20 \text{ Vdc}$ , $V_{GS} = 5.0 \text{ Vdc}$ , Peak $I_L = 7.5 \text{ Apk}$ , $L = 6 \text{ mH}$ , $R_G = 25 \Omega$ )	$E_{AS}$	169	mJ
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	$T_L$	260	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Mounted onto a 2" square FR-4 Board (1" sq. 2 oz Cu 0.06" thick single sided),  $t \leq 10$  seconds.
2. Mounted onto a 2" square FR-4 Board (1" sq. 2 oz Cu 0.06" thick single sided),  $t =$  steady state.
3. Minimum FR-4 or G-10 PCB,  $t =$  Steady State.
4. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle = 2%.

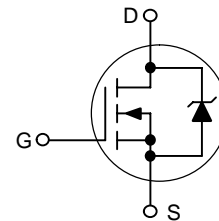


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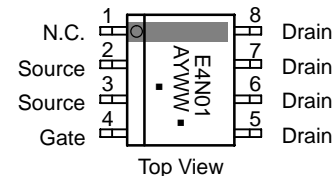
**4.2 AMPERES, 20 VOLTS**  
**0.045  $\Omega$  @  $V_{GS} = 4.5 \text{ V}$**

##### Single N-Channel



**SO-8**  
**CASE 751**  
**STYLE 13**

##### MARKING DIAGRAM AND PIN ASSIGNMENT



E4N01 = Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

##### ORDERING INFORMATION

Device	Package	Shipping†
NTMS4N01R2	SO-8	2500 / Tape & Reel
NTMS4N01R2G	SO-8 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NTMS4N01R2

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted) (Note 5)

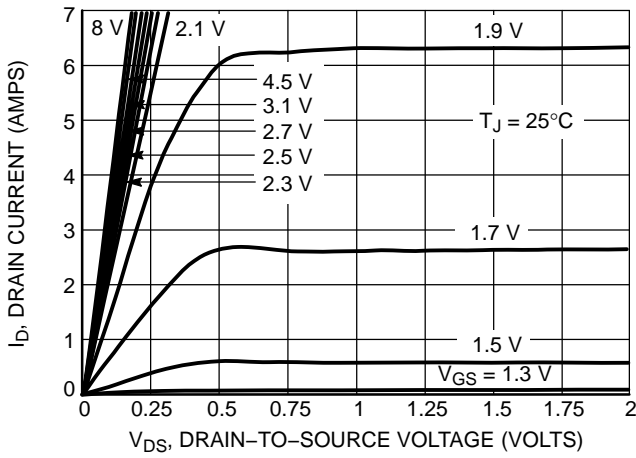
Characteristic	Symbol	Min	Typ	Max	Unit	
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage (V <sub>GS</sub> = 0 Vdc, I <sub>D</sub> = 250 μAdc)	V <sub>(BR)DSS</sub>	20	–	–	Vdc	
Temperature Coefficient (Positive)		–	20	–	mV/°C	
Zero Gate Voltage Drain Current (V <sub>DS</sub> = 12 Vdc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 25°C) (V <sub>DS</sub> = 12 Vdc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 125°C) (V <sub>DS</sub> = 20 Vdc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 25°C)	I <sub>DSS</sub>	–	–	1.0	μAdc	
		–	–	10		
		–	0.2	–		
Gate-Body Leakage Current (V <sub>GS</sub> = +10 Vdc, V <sub>DS</sub> = 0 Vdc)	I <sub>GSS</sub>	–	–	100	nAdc	
Gate-Body Leakage Current (V <sub>GS</sub> = -10 Vdc, V <sub>DS</sub> = 0 Vdc)	I <sub>GSS</sub>	–	–	-100	nAdc	
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage (V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μAdc)	V <sub>GS(th)</sub>	0.6	0.95	1.2	Vdc	
Temperature Coefficient (Negative)		–	-3.0	–	mV/°C	
Static Drain-to-Source On-State Resistance (V <sub>GS</sub> = 4.5 Vdc, I <sub>D</sub> = 4.2 Adc) (V <sub>GS</sub> = 2.7 Vdc, I <sub>D</sub> = 2.1 Adc) (V <sub>GS</sub> = 2.5 Vdc, I <sub>D</sub> = 2.0 Adc)	R <sub>DS(on)</sub>	–	0.030	0.04	Ω	
		–	0.035	0.05		
		–	0.037	–		
Forward Transconductance (V <sub>DS</sub> = 2.5 Vdc, I <sub>D</sub> = 2.0 Adc)	g <sub>FS</sub>	–	10	–	Mhos	
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	(V <sub>DS</sub> = 10 Vdc, V <sub>GS</sub> = 0 Vdc, f = 1.0 MHz)	C <sub>ISS</sub>	–	870	1200	pF
Output Capacitance		C <sub>OSS</sub>	–	260	400	
Reverse Transfer Capacitance		C <sub>RSS</sub>	–	60	100	
<b>SWITCHING CHARACTERISTICS (Notes 6 &amp; 7)</b>						
Turn-On Delay Time	(V <sub>DD</sub> = 12 Vdc, I <sub>D</sub> = 4.2 Adc, V <sub>GS</sub> = 4.5 Vdc, R <sub>G</sub> = 2.3 Ω)	t <sub>d(on)</sub>	–	13	25	ns
Rise Time		t <sub>r</sub>	–	35	65	
Turn-Off Delay Time		t <sub>d(off)</sub>	–	45	75	
Fall Time		t <sub>f</sub>	–	50	90	
Total Gate Charge	(V <sub>DS</sub> = 12 Vdc, V <sub>GS</sub> = 4.5 Vdc, I <sub>D</sub> = 4.2 Adc)	Q <sub>tot</sub>	–	11	16	nC
Gate-Source Charge		Q <sub>gs</sub>	–	2.0	–	
Gate-Drain Charge		Q <sub>gd</sub>	–	3.0	–	
<b>BODY-DRAIN DIODE RATINGS (Note 6)</b>						
Diode Forward On-Voltage (I <sub>S</sub> = 4.2 Adc, V <sub>GS</sub> = 0 Vdc) (I <sub>S</sub> = 4.2 Adc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 125°C)	V <sub>SD</sub>	–	0.85	1.1	Vdc	
		–	0.70	–		
Reverse Recovery Time	(I <sub>S</sub> = 4.2 Adc, V <sub>GS</sub> = 0 Vdc, di <sub>S</sub> /dt = 100 A/μs)	t <sub>rr</sub>	–	20	–	ns
		t <sub>a</sub>	–	12	–	
		t <sub>b</sub>	–	8.0	–	
Reverse Recovery Stored Charge	Q <sub>RR</sub>	–	0.01	–	μC	

5. Handling precautions to protect against electrostatic discharge is mandatory.

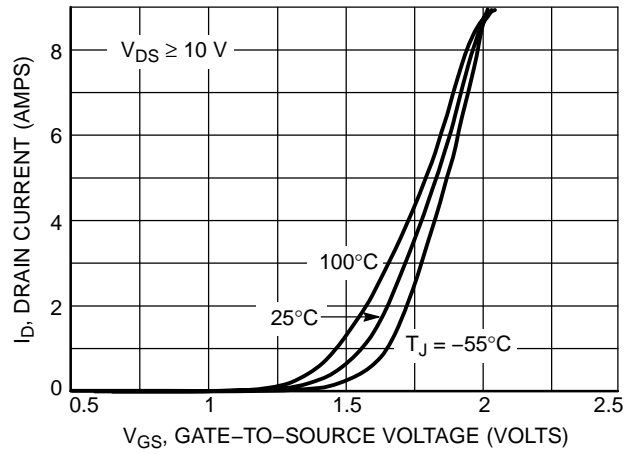
6. Indicates Pulse Test: Pulse Width = 300 μs max, Duty Cycle = 2%.

7. Switching characteristics are independent of operating junction temperature.

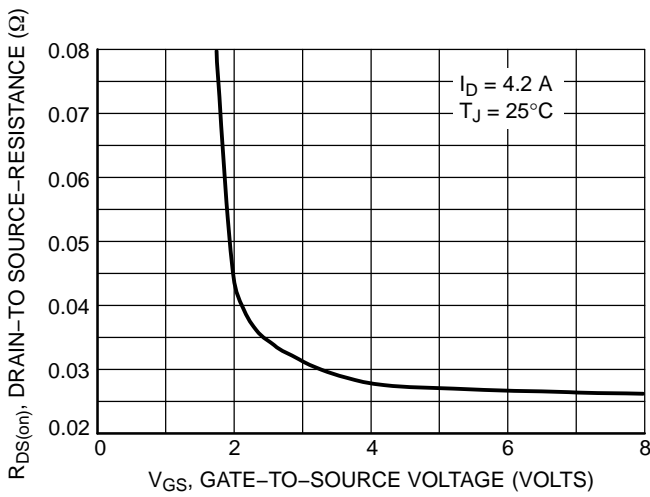
# NTMS4N01R2



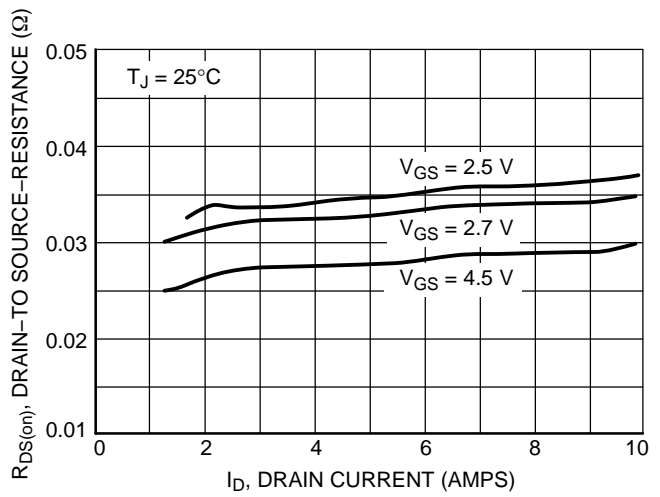
**Figure 1. On-Region Characteristics**



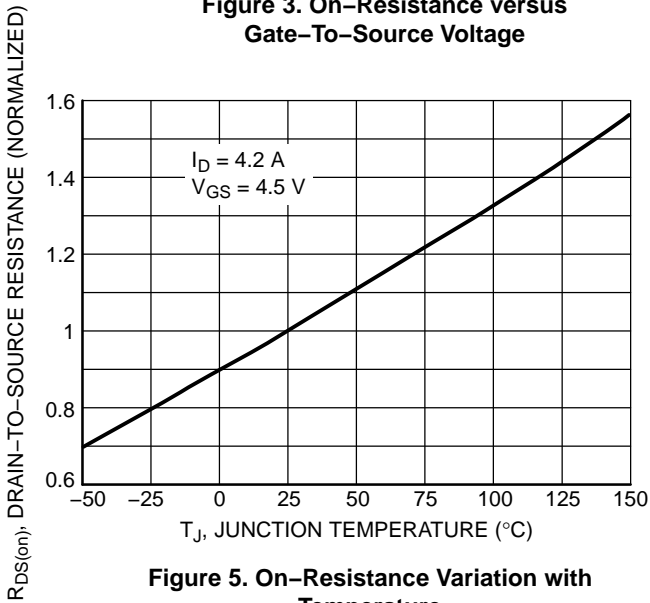
**Figure 2. Transfer Characteristics**



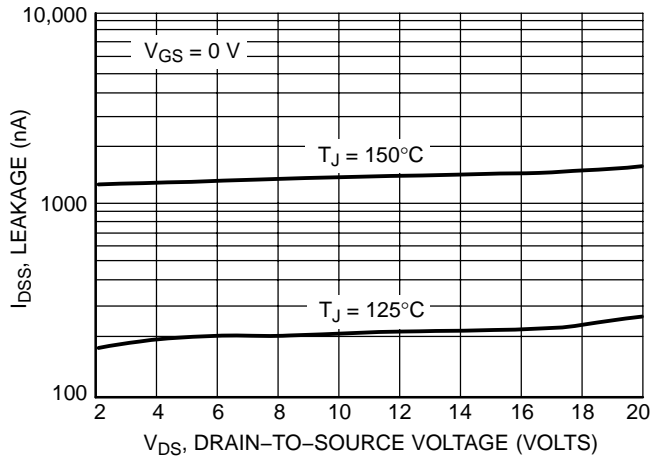
**Figure 3. On-Resistance versus Gate-to-Source Voltage**



**Figure 4. On-Resistance versus Drain Current and Gate Voltage**



**Figure 5. On-Resistance Variation with Temperature**



**Figure 6. Drain-to-Source Leakage Current versus Voltage**

# NTMS4N01R2

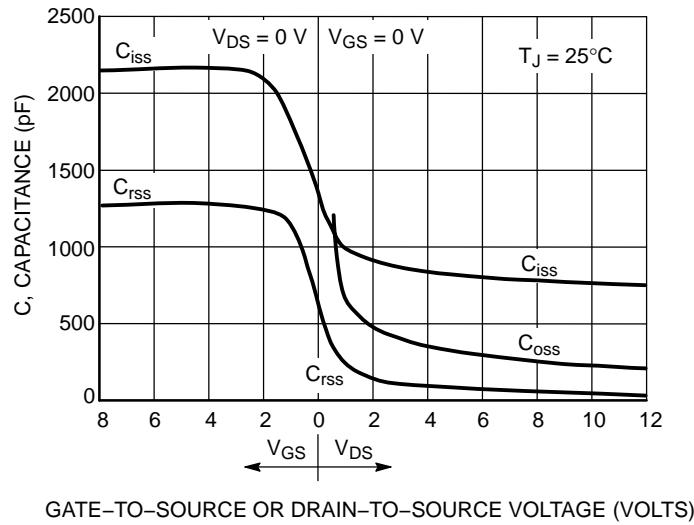


Figure 7. Capacitance Variation

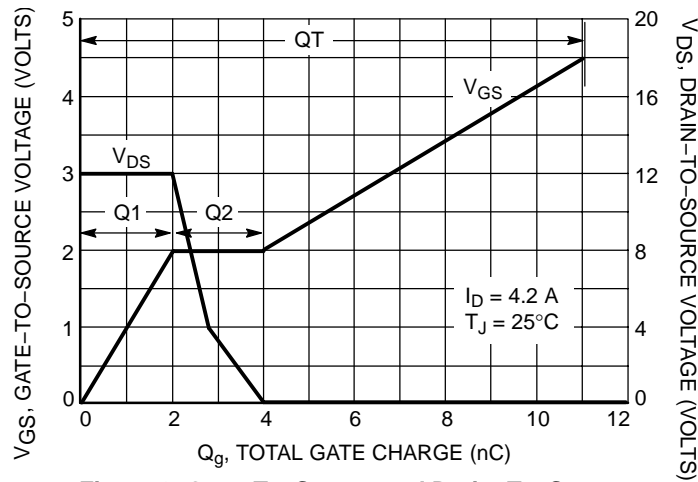


Figure 8. Gate-To-Source and Drain-To-Source Voltage versus Total Charge

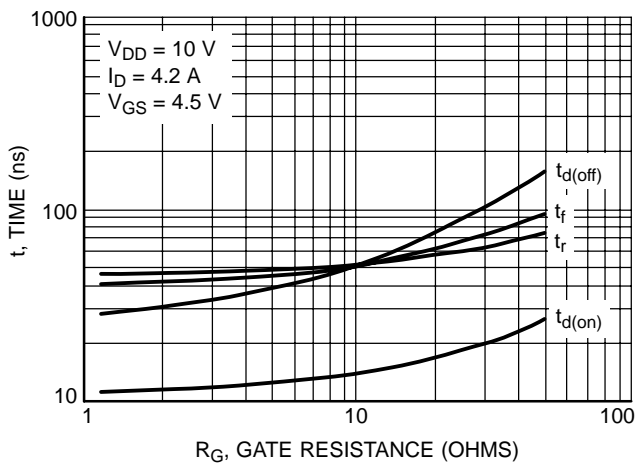


Figure 9. Resistive Switching Time Variation versus Gate Resistance

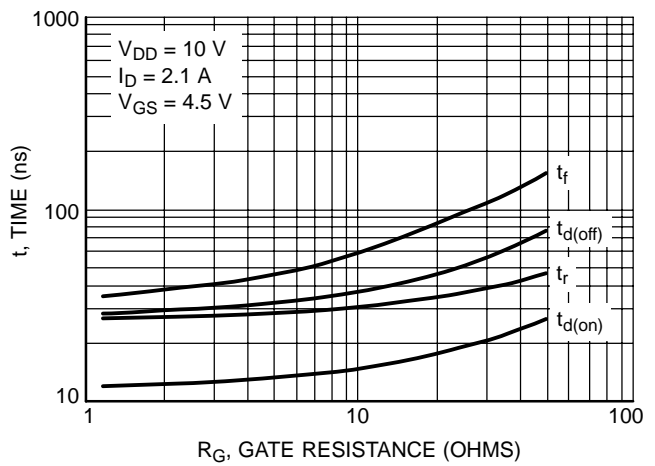


Figure 10. Resistive Switching Time Variation versus Gate Resistance

# NTMS4N01R2

## DRAIN-TO-SOURCE DIODE CHARACTERISTICS

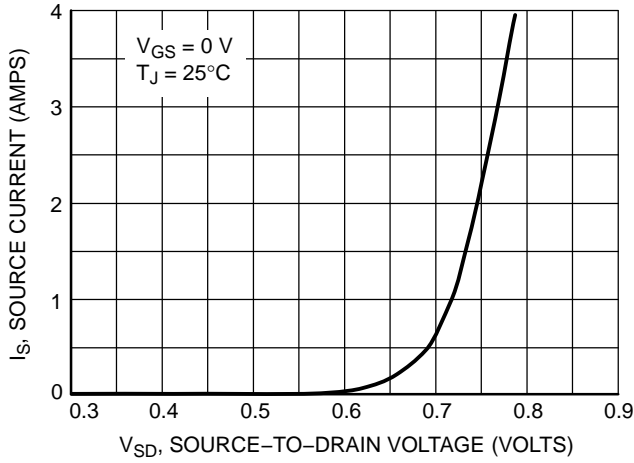


Figure 11. Diode Forward Voltage versus Current

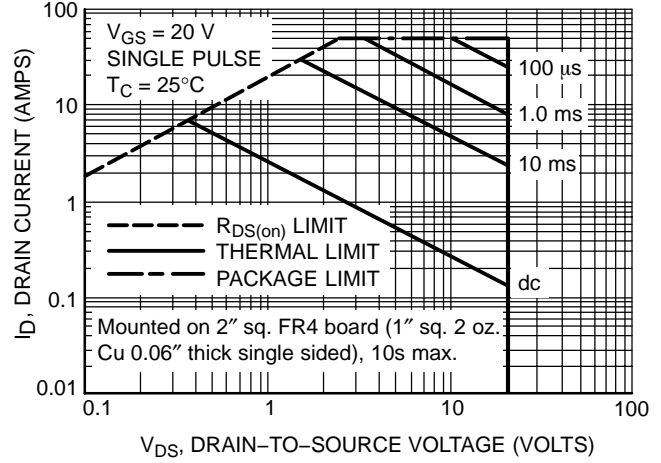


Figure 12. Maximum Rated Forward Biased Safe Operating Area

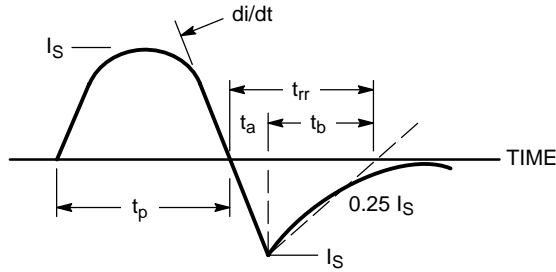


Figure 13. Diode Reverse Recovery Waveform

## TYPICAL ELECTRICAL CHARACTERISTICS

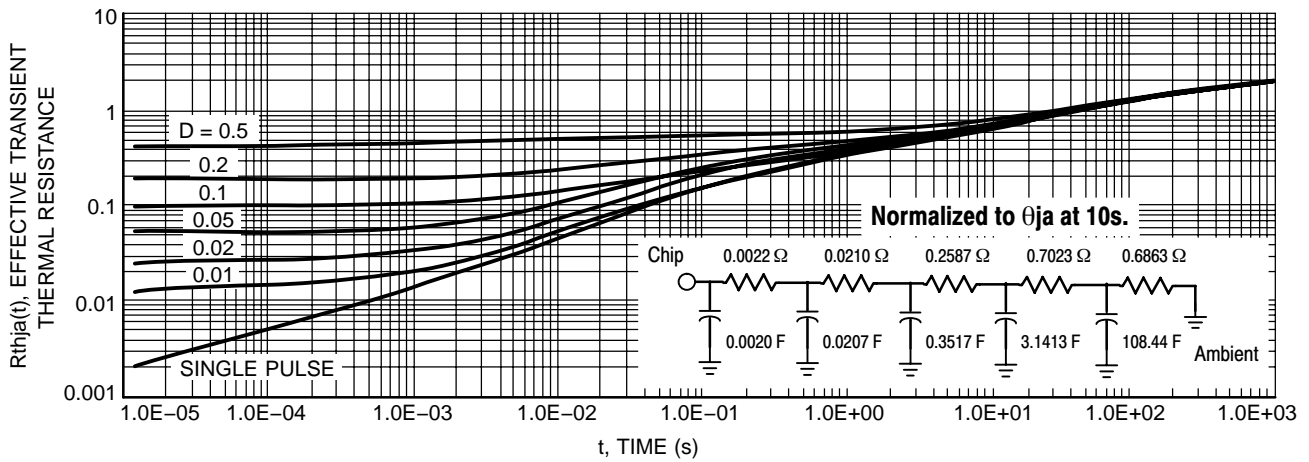
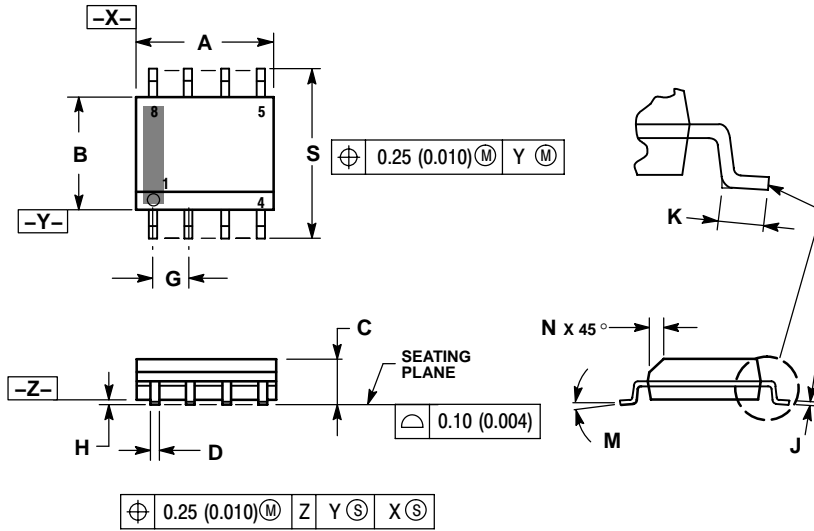


Figure 14. Thermal Response

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## PACKAGE DIMENSIONS

SOIC-8 NB  
CASE 751-07  
ISSUE AG



**NOTES:**

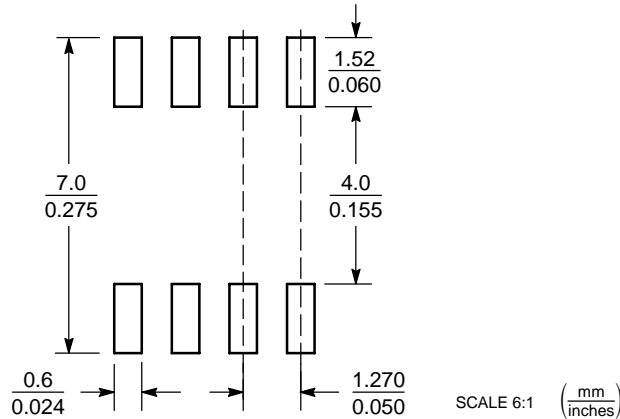
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

**STYLE 13:**

- PIN 1: N.C.  
 2. SOURCE  
 3. SOURCE  
 4. GATE  
 5. DRAIN  
 6. DRAIN  
 7. DRAIN  
 8. DRAIN

**SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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